

Radiographic Analysis of a X-Ray Semiconductor Detector with a Digital Sensor for the Determination of its Efficiency

MSilva¹, SHerdade¹, DNersissian², MPereira², PCosta², RTerini*³, (1) Instituto de Física, Universidade de São Paulo, São Paulo, SP, Brazil, (2) Instituto de Eletrotécnica e Energia, Universidade de São Paulo, SP, Brazil, (3) Departamento de Física, Pontifícia Universidade Católica de São Paulo, São Paulo, Brazil

Poster Session: TH-CXH-02 Poster Session: Diagnostic Physics, Medical Imaging, and Image Processing - Projection Imaging/Quality Assurance/Ultrasound

Track: 01 Diagnostic Physics, Medical Imaging, and Image Processing

In order to completely characterize photon beams emitted by an X-ray tube, one must have knowledge of the energy spectra. This characterization can be made utilizing spectrometers based on silicon photodiodes, which are more practical and less expensive than germanium detectors. For this objective, it is necessary to correct the measured spectra for the change with photon energy of the detector total efficiency, which depends on the photodiode window thickness, among other factors. The present work describes the evaluation of the unknown borosilicate glass window thickness of a Hamamatsu S3071 PIN photodiode, using radiographic images obtained with a X-ray sensitive CCD sensor, utilized in dental radiography. With the help of a dedicated software, it was possible to make a graphical analysis of the contrast of several images produced through the irradiation of the isolated photodiode with a X-ray beam, at several sets of tube potential, current-time product and additional filtration. The most sharp images were utilized to determine the detector window thickness, which average value was 0.41 ± 0.01 mm, corresponding to 9.1 ± 0.3 image pixels. With such value, it was corrected the energy spectra of the radiation emitted from radioactive sources of ^{133}Ba and ^{241}Am . It was obtained the relative photon intensities, for the ^{133}Ba , as 0.058 for I (26.345 keV)/I (59.537 keV) through the corrected spectrum, against 0.056 from the literature data; for ^{133}Ba , we obtained respectively 4.2 against 4.4 for I (30.973 keV)/I (34.987 + 36.005 keV). This research was partially supported by FAPESP.

TRABALHO APRESENTADO NO: World
Congress on Medical Physics and
Biomedical, Chicago – 2000. (temos CD-
ROM na servidora)